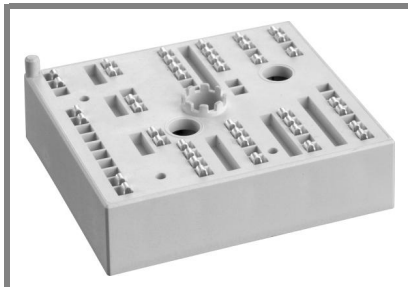


# SKiIP 29AHB08V1



MiniSKiIP<sup>®</sup> 2

3-phase bridge rectifier +  
brake chopper

SKiIP 29AHB08V1

## Features

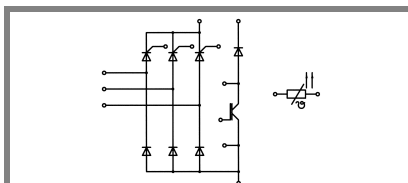
- Ultrafast NPT IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

## Typical Applications

- Input bridge for Inverter up to 30 kVA

## Remarks

- $V_{CEsat}$ ,  $V_F$  = chip level value



AHB

Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT - Chopper</b>			
$V_{CES}$		600	V
$I_C$	$T_s = 25 (70)^\circ\text{C}$	125 (93)	A
$I_{CRM}$	$t_p \leq 1 \text{ ms}$	300	A
$V_{GES}$		$\pm 15$	V
$T_j$		- 40 ... + 150	$^\circ\text{C}$
<b>Diode - Chopper</b>			
$I_F$	$T_s = 25 (70)^\circ\text{C}$	120 (89)	A
$I_{FRM}$	$t_p \leq 1 \text{ ms}$	300	A
$T_j$		- 40 ... + 150	$^\circ\text{C}$
<b>Diode / Thyristor - Rectifier</b>			
$V_{RRM}$		800	V
$I_F / I_T$	$T_s = 70$	82	A
$I_{FSM} / I_{TSM}$	$t_p = 10 \text{ ms}$ , $\sin 180^\circ$ , $T_j = 25^\circ\text{C}$	1000	A
$i^2t$	$t_p = 10 \text{ ms}$ , $\sin 180^\circ$ , $T_j = 25^\circ\text{C}$	5500	$\text{A}^2\text{s}$
$T_j$	Diode	- 40 ... + 150	$^\circ\text{C}$
$T_j$	Thyristor	- 40 ... + 125	$^\circ\text{C}$
$I_{IRMS}$	per power terminal (20 A / spring)	120	A
$T_{stg}$	$T_{op} \leq T_{stg}$	- 40 ... + 125	$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500	V

Characteristics		$T_s = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT - Chopper</b>					
$V_{CEsat}$	$I_{Cnom} = 150 \text{ A}$ , $T_j = 25 (125)^\circ\text{C}$		2 (2,2)	2,5 (2,7)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 3 \text{ mA}$	3	4	5	V
$V_{CE(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1,2 (1,1)	1,3 (1,2)	V
$r_T$	$T_j = 25 (125)^\circ\text{C}$		5,3 (7,3)	8 (10)	m $\Omega$
$C_{ies}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		9		nF
$C_{oes}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		1,7		nF
$C_{res}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		2,1		nF
$R_{th(j-s)}$	per IGBT		0,4		K/W
$t_{d(on)}$	under following conditions		20		ns
$t_r$	$V_{CC} = 300 \text{ V}$ , $V_{GE} = \pm 15 \text{ V}$		25		ns
$t_{d(off)}$	$I_{Cnom} = 150 \text{ A}$ , $T_j = 125^\circ\text{C}$		185		ns
$t_f$	$R_{Gon} = R_{Goff} = 4 \Omega$		15		ns
$E_{on}$	inductive load		5,7		mJ
$E_{off}$			3,7		mJ
<b>Diode - Chopper</b>					
$V_F = V_{EC}$	$I_{Fnom} = 150 \text{ A}$ , $T_j = 25 (125)^\circ\text{C}$		1,7 (1,7)	2,1 (2,1)	V
$V_{(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,9)	1,1 (1)	V
$r_T$	$T_j = 25 (125)^\circ\text{C}$		4,7 (5,3)	6,7 (7,3)	m $\Omega$
$R_{th(j-s)}$	per diode		0,55		K/W
$I_{RRM}$	under following conditions		270		A
$Q_{rr}$	$I_{Fnom} = 150 \text{ A}$ , $V_R = 300 \text{ V}$		18		$\mu\text{C}$
$E_{rr}$	$V_{GE} = 0 \text{ V}$ , $T_j = 125^\circ\text{C}$		3,5		mJ
	$di_F/dt = 13700 \text{ A}/\mu\text{s}$				

Characteristics		$T_s = 25\text{ °C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>Diode - Rectifier</b>					
$V_F$	$I_{Fnom} = 75\text{ A}$ , $T_j = 25\text{ °C}$		1,2		V
$V_{(TO)}$	$T_j = 150\text{ °C}$		0,8		V
$r_T$	$T_j = 150\text{ °C}$		7		mΩ
$R_{th(j-s)}$	per diode		0,7		K/W
<b>Thyristor - Rectifier</b>					
$V_T$	$I_{Fnom} = 120\text{ A}$ , $T_j = 25\text{ (125) °C}$			1,8 (1,7)	V
$V_{T(TO)}$	$T_j = 125\text{ °C}$			1,1	V
$r_T$	$T_j = 125\text{ °C}$			5	mΩ
$V_{GT}$	$T_j = 25\text{ °C}$			3	V
$I_{GT}$	$T_j = 25\text{ °C}$	150			mA
$I_H$	$T_j = 25\text{ °C}$		200		mA
$I_L$	$T_j = 25\text{ °C}$		400		mA
$dv/dt_{(cr)}$	$T_j = 125\text{ °C}$			1000	V/μs
$di/dt_{(cr)}$	$T_j = 125\text{ °C}$			50	A/μs
$R_{th(j-s)}$	per thyristor		0,65		K/W
<b>Temperature Sensor</b>					
$R_{ts}$	3 %, $T_r = 25\text{ (100) °C}$		1000(1670)		Ω
<b>Mechanical Data</b>					
w			65		g
$M_s$	Mounting torque	2		2,5	Nm

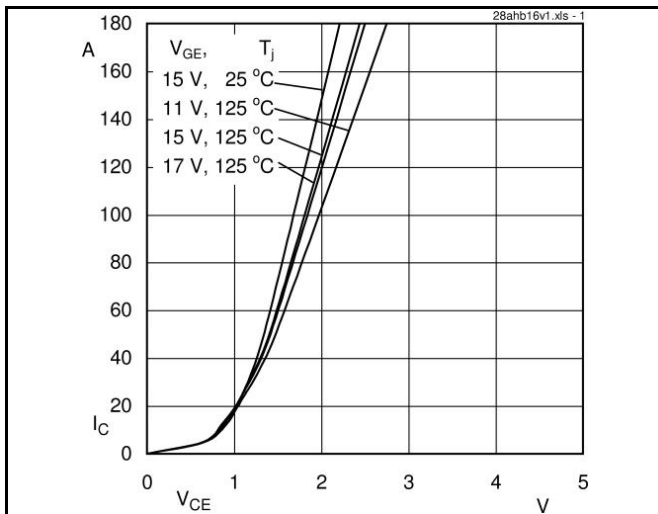


Fig. 1 Typ. output characteristic

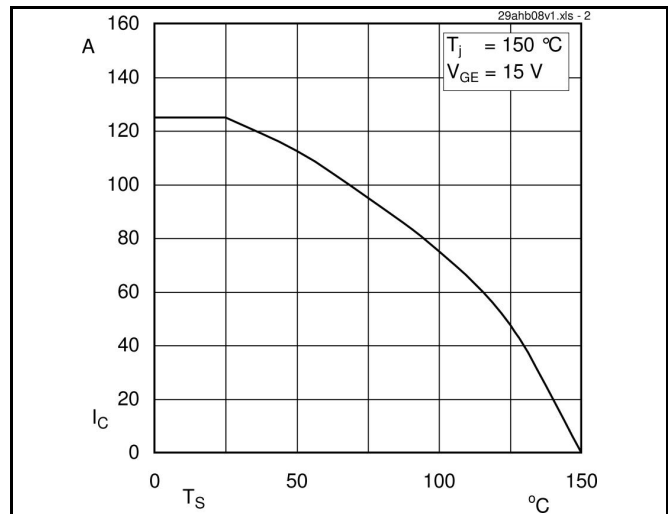


Fig. 2 Typ. rated current vs. temperature

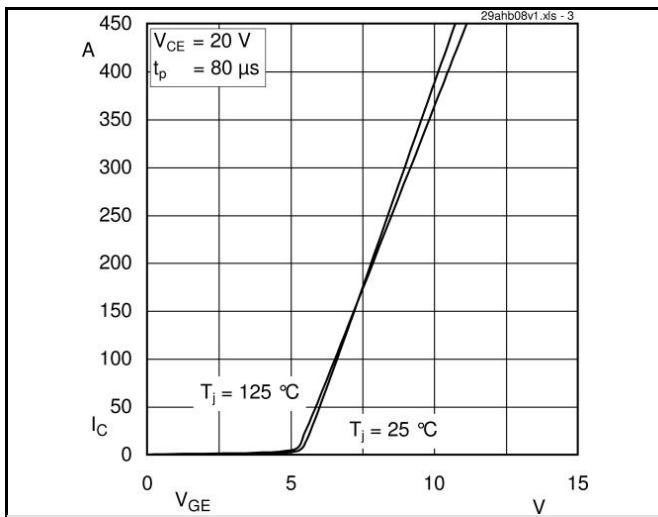


Fig. 3 Typ. transfer characteristic

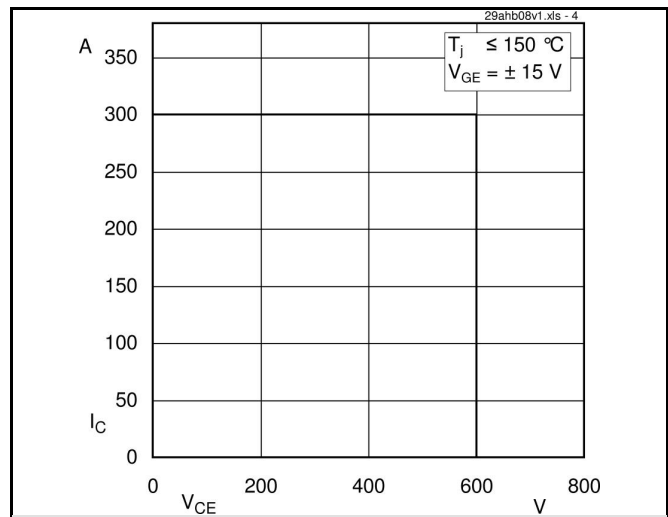


Fig. 4 Reverse bias safe operating area

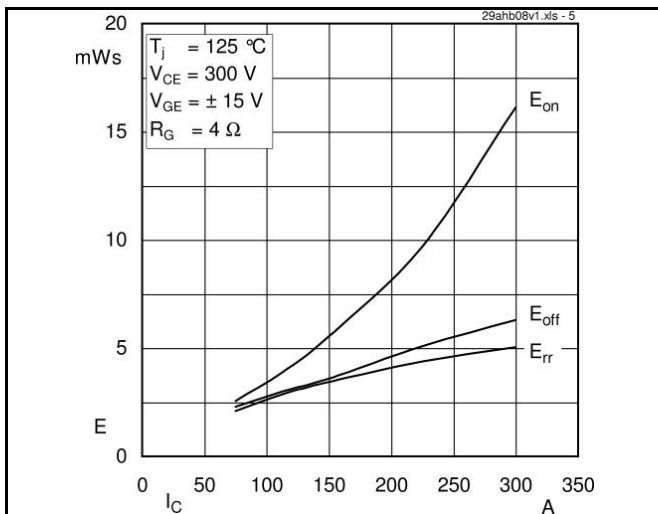


Fig. 5 Typ. Turn-on /-off energy =  $f(I_C)$

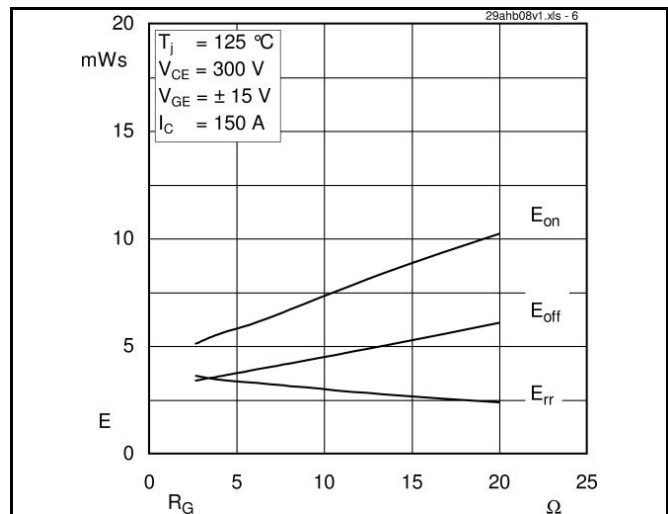


Fig. 6 Typ. Turn-on /-off energy =  $f(R_G)$

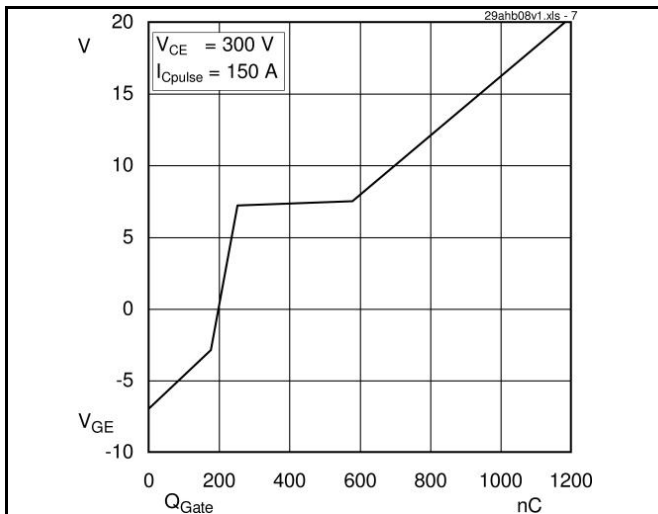


Fig. 7 Typ. gate charge characteristic

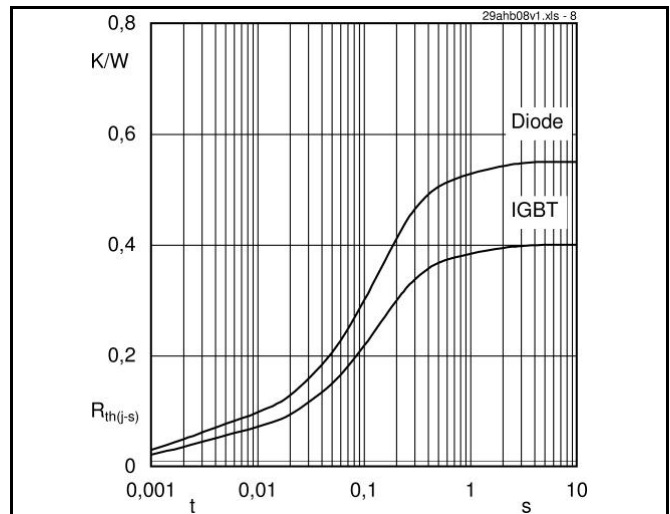


Fig. 8 Typ. thermal impedance

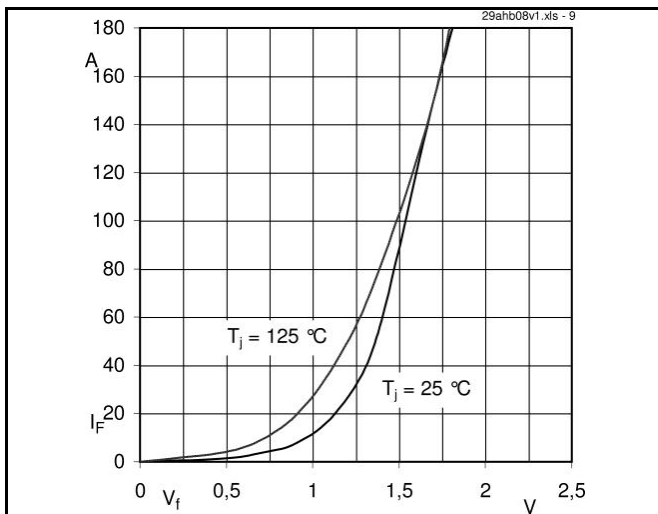


Fig. 9 Typ. freewheeling diode forward characteristic

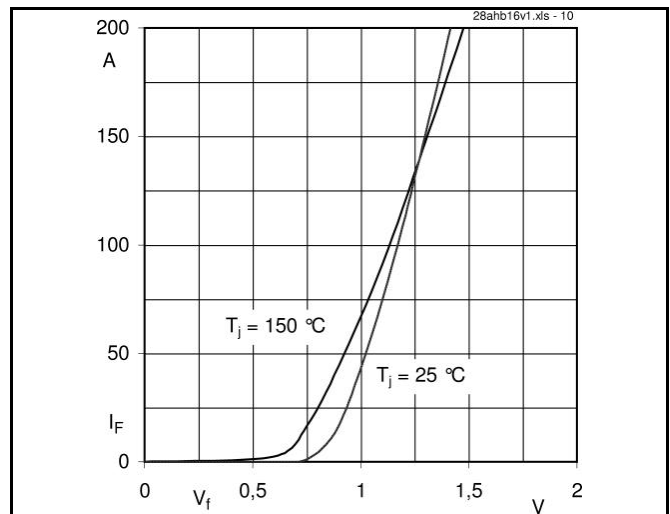


Fig. 10 Typ. input bridge forward characteristic

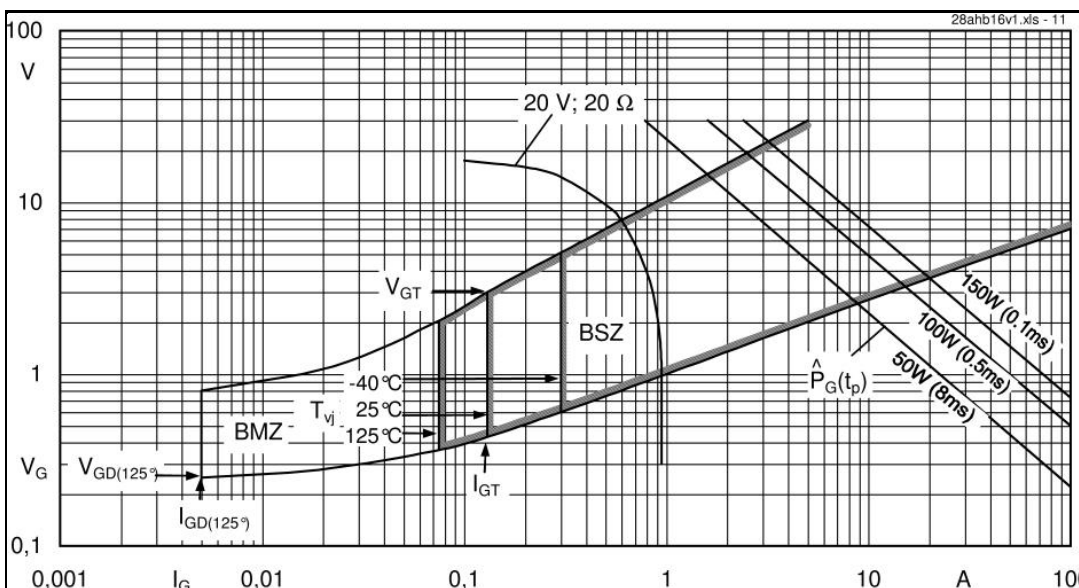
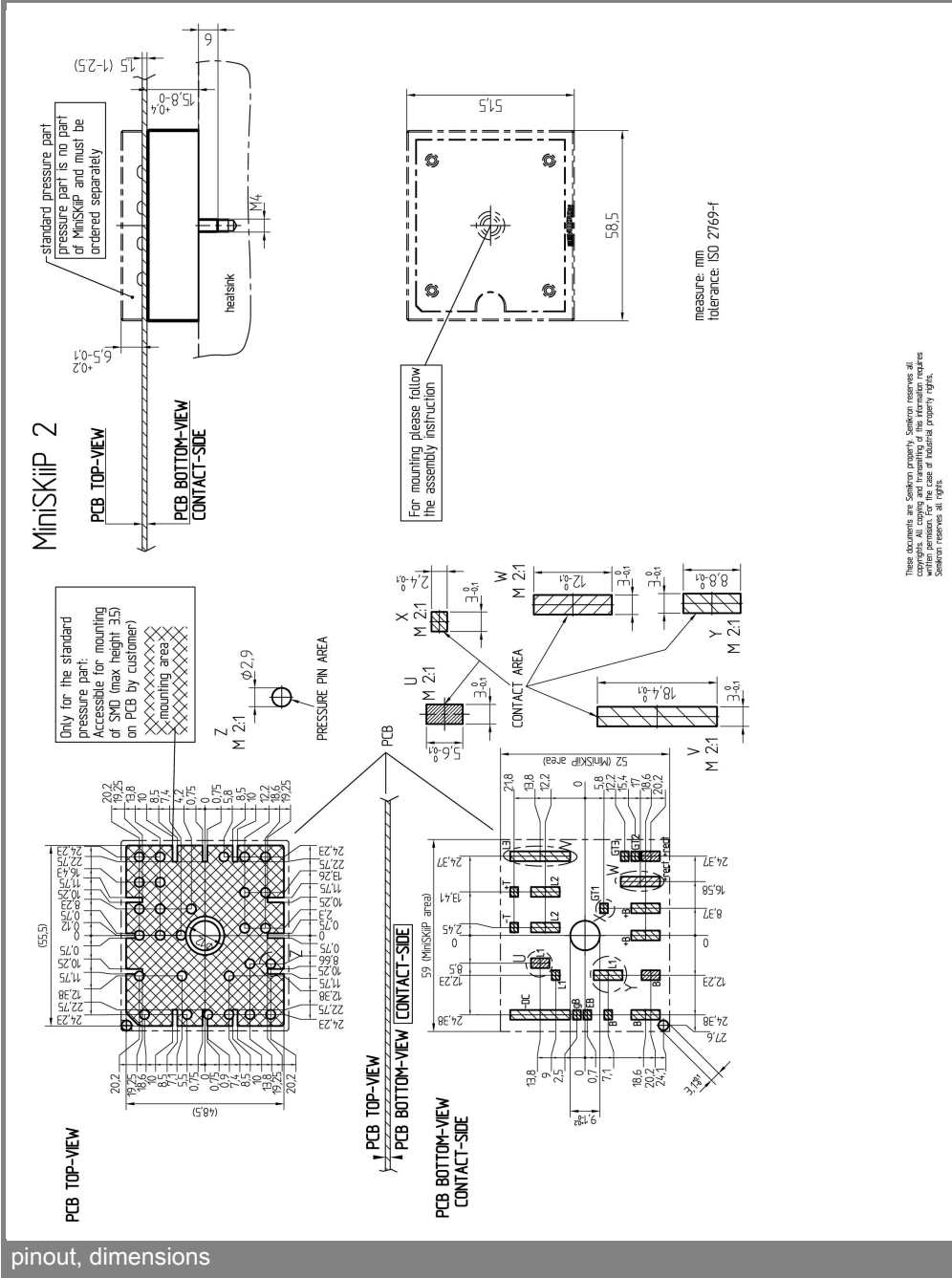
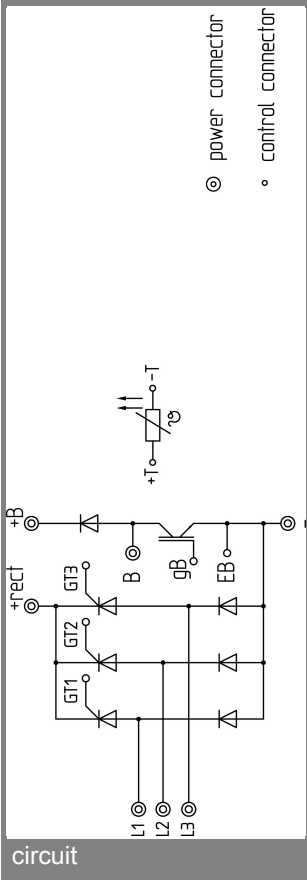


Fig. 11 Typ. gate trigger characteristic



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